PROCESS CP108

Schottky Rectifier

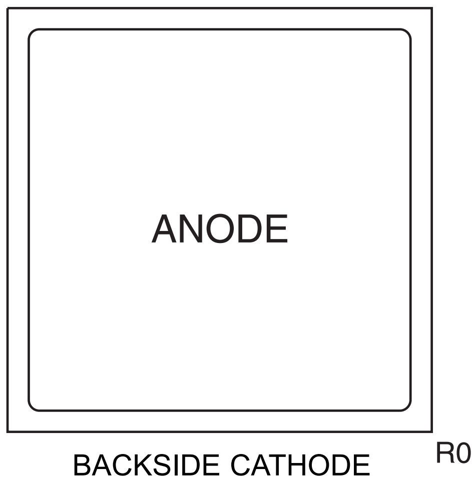
Schottky Barrier Rectifier Chip - 2.0 Amp

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	52 X 52 MILS
Die Thickness	9 MILS
Anode Bonding Pad Area	47 X 47 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
5,110

PRINCIPAL DEVICE TYPES
1N5817
1N5818
1N5819
CXSH-4
CZSH-4

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PROCESS CP108

Typical Electrical Characteristics

The Typical Electrical Characteristics data
for this chip is currently being revised.

For the latest updated data for this Chip Process,
please visit our website at:

www.centralsemi.com/chip

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